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AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1. (Currently Amended) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

- (a) forming a first insulative film of a single layer or a stacked layer ~~on~~ over a surface of a semiconductor wafer;
- (b) removing the first insulative film on an edge of the semiconductor wafer;
- (c) patterning the first insulative film after the step (b);
- (d) etching the semiconductor wafer by using the first insulative film as a mask after the step (c);
- (e) forming a second insulative film ~~on~~ over the semiconductor wafer including a portion ~~on~~ over the first insulative film after the step (d); and
- (f) mechanically and chemically polishing a surface of the second insulative film, thereby planarizing the surface thereof.

2. (Original) A fabrication method of a semiconductor integrated circuit device according to claim 1, wherein the step (b) is conducted by polishing with a polishing means using a slurry or a grinding wheel.

3. (Original) A fabrication method of a semiconductor integrated circuit device according to claim 2, wherein the polishing means has plural polishing drums in which each of the plural polishing drums are in contact with the edge of the

501.41261X00

semiconductor wafer in a region different from each other and the angle of contact changes in accordance with the shape of the edge of the semiconductor wafer.

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